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NOTICE OF ALLOWANCE AND FEE(S) DUE

29673 7590 07/16/2009 STEVENS & SHOWALTER LLP 7019 CORPORATE WAY DAYTON, OH 45459-4238 EXAMINER
AHMADI, MOHSEN
ART UNIT PAPER NUMBER
2812

DATE MAILED: 07/16/2009

| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
|-----------------|-------------|----------------------|---------------------|------------------|
| 10/586,621 | 08/18/2008 | Ralf Lerner | LEO 008 PA | 6530 |

TITLE OF INVENTION: PASSIVATION OF DEEP ISOLATING SEPARATING TRENCHES WITH SUNK COVERING LAYERS

| APPLN. TYPE | SMALL ENTITY | ISSUE FEE DUE | PUBLICATION FEE DUE | PREV. PAID ISSUE FEE | TOTAL FEE(S) DUE | DATE DUE |
|----------------|--------------|---------------|---------------------|----------------------|------------------|------------|
| nonprovisional | NO | \$1510 | \$300 | \$0 | \$1810 | 10/16/2009 |

THE APPLICATION IDENTIFIED ABOVE HAS BEEN EXAMINED AND IS ALLOWED FOR ISSUANCE AS A PATENT. PROSECUTION ON THE MERITS IS CLOSED. THIS NOTICE OF ALLOWANCE IS NOT A GRANT OF PATENT RIGHTS. THIS APPLICATION IS SUBJECT TO WITHDRAWAL FROM ISSUE AT THE INITIATIVE OF THE OFFICE OR UPON PETITION BY THE APPLICANT. SEE 37 CFR 1.313 AND MPEP 1308.

THE ISSUE FEE AND PUBLICATION FEE (IF REQUIRED) MUST BE PAID WITHIN THREE MONTHS FROM THE MAILING DATE OF THIS NOTICE OR THIS APPLICATION SHALL BE REGARDED AS ABANDONED. THIS STATUTORY PERIOD CANNOT BE EXTENDED. SEE 35 U.S.C. 1SI. THE ISSUE FEE DUE INDICATED ABOVE DOES NOT REFLECT A CREDIT FOR ANY PREVIOUSLY PAID ISSUE FEE IN THIS APPLICATION. IF AN ISSUE FEE HAS PREVIOUSLY BEEN PAID IN THIS APPLICATION (AS SHOWN ABOVE), THE RETURN OF PART B OF THIS FORM WILL BE CONSIDERED A REQUEST TO REAPPLY THE PREVIOUSLY PAID ISSUE FEE TOWARD THE ISSUE FEE NOW DUE.

HOW TO REPLY TO THIS NOTICE:

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If the SMALL ENTITY is shown as YES, verify your current SMALL ENTITY status:

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B. If the status above is to be removed, check box 5b on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and twice the amount of the ISSUE FEE shown above, or

If the SMALL ENTITY is shown as NO:

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II. PART B - FEE(S) TRANSMITTAL, or its equivalent, must be completed and returned to the United States Patent and Trademark Office (USPTO) with your ISSUE FEE and PUBLICATION FEE (if required). If you are charging the fee(s) to your deposit account, section "4b" of Part B - Fee(s) Transmittal should be completed and an extra copy of the form should be submitted. If an equivalent of Part B is filed, a request to reapply a previously paid issue fee must be clearly made, and delays in processing may occur due to the difficulty in recognizing the paper as an equivalent of Part B.

III. All communications regarding this application must give the application number. Please direct all communications prior to issuance to Mail Stop ISSUE FEE unless advised to the contrary.

IMPORTANT REMINDER: Utility patents issuing on applications filed on or after Dec. 12, 1980 may require payment of maintenance fees. It is patentee's responsibility to ensure timely payment of maintenance fees when due.

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| AHMADI, | MOHSEN | | 2812 | 438-424000 | | | | | | |
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| | SMALL ENTITY state | ıs. See | 37 CFR 1.27. | | | | | TITY status. Sec 37 Cl | | |
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| Typed or printed name | | | | Registration No. | | | | | | |
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| STEVENS & SHOWALTER LLP | | ALTER LLP | | AHMADI, MOHSEN | | |
| 7019 CORPORA | | | | ART UNIT | PAPER NUMBER | |
| DAYTON, OH 45459-4238 | | | | 2812 | | |
| | | | | DATE MAILED: 07/16/2009 | | |

Determination of Patent Term Adjustment under 35 U.S.C. 154 (b)

(application filed on or after May 29, 2000)

The Patent Term Adjustment to date is 0 day(s). If the issue fee is paid on the date that is three months after the mailing date of this notice and the patent issues on the Tuesday before the date that is 28 weeks (six and a half months) after the mailing date of this notice, the Patent Term Adjustment will be 0 day(s).

If a Continued Prosecution Application (CPA) was filed in the above-identified application, the filing date that determines Patent Term Adjustment is the filing date of the most recent CPA.

Applicant will be able to obtain more detailed information by accessing the Patent Application Information Retrieval (PAIR) WEB site (http://pair.uspto.gov).

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (571)-272-7702. Questions relating to issue and publication fee payments should be directed to the Customer Service Center of the Office of Patent Publication at 1-(888)-786-0101 or (571)-272-4200.

Interview Summary

 Application No.
 Applicant(s)

 10/586,621
 LERNER ET AL.

 Examiner
 Art Unit

 MOHSEN AHMADI
 2812

All participants (applicant, applicant's representative, PTO personnel):

| (1) MOHSEN AHMADI(PTO personnel). | (3)Mulpuri Savitri (Primary Examiner). |
|--|--|
| (2) Richard C Stevens reg#28046(app's representative). | (4) |
| Date of Interview: 06 July 2009. | |
| Type: a)⊠ Telephonic b)□ Video Conference c)□ Personal [copy given to: 1)□ applicant | 2) applicant's representative] |
| Exhibit shown or demonstration conducted: d) Yes If Yes, brief description: | e)⊠ No. |
| Claim(s) discussed: <u>1,21, 26,31 and 33</u> . | |
| Identification of prior art discussed: <u>none</u> . | |
| Agreement with respect to the claims f) $\!$ | g) was not reached. h) N/A. |
| In condition for allowance. (A fuller description, if necessary, and a copy of the amer allowable, if available, must be attached. Also, where no allowable is available, a summary thereof must be attach. THE FORMAL WRITTEN REPLY TO THE LAST OFFICE INTERVIEW. (See MPEP Section 713.04). If a reply to the GIVEN A NON-EXTENDABLE PERIOD OF THE LONGE. | s agreed to amend claims 1 and 31 to incorporate the immend claim 26 and cancel claims 27-28 to place application and the summer agreed would render the claims copy of the amendments that would render the claims ed.) ACTION MUST INCLUDE THE SUBSTANCE OF THE the last office action has already been filed, APPLICANT IS R OF ONE MONTH OR THIRTY DAY'S FROM THIS TERRYIEW SUMMARY FORM, WHICHEVER IS LATER, TO |
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| AINS) CLOSED in this app propriate communication is application is subject to | lication. If not include will be mailed in due | ed course. THIS |
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| 6. ☑ Interview Summary of Paper No./Mail Date 7. ☑ Examiner's Amendre 8. ☑ Examiner's Stateme 9. ☐ Other /Charles D. Garber/ | (PTO-413), e <u>07/06/2009</u> . nent/Comment nt of Reasons for Allo | |
| | ANNS) CLOSED in this appropriate communication is application is subject to p 1308. S.C. § 119(a)-(d) or (f). Sived. Sived in Application No ave been received in this received in the control of the control of the received in the control of the control of the received in this received in the received in this received in the received in th | LERNER ET AL. ILERNER ET AL. Art Unit 2812 2812 2812 2812 2812 2812 2812 2816 2816 2816 2816 2817 3816 3 |

Art Unit: 2812

Drawings/Examiners Comment

The drawings filed on August 08, 2008 are acceptable subject to correction of the

informalities indicated as follows:

Figure 1 should be designated by a more legible legend such as -- Prior Art--

because only that which is old is illustrated. See MPEP § 608.02(g).

The line, numbers, and letters of Figures 1-4 must be durable, clean, sufficiently

dense and dark, and uniformly thick and well-defined should be. See 37 CFR 1.84(I)

In order to avoid abandonment of this application, correction is required in reply

to the Office action. The correction will not be held in abeyance.

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes

and/or additions be unacceptable to applicant, an amendment may be filed as provided

by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be

submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview

with Attorney Richard C. Stevens on 07/07/2007.

Cancel claims 21, 27-28 and 33.

Replace claim 1, with the following:

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1. (Currently Amended) A method of forming a wafer for integrated circuits comprising low voltage elements and high voltage elements, wherein chip regions of different potentials are separated by dielectrically insulating regions formed as isolation trenches extending downward from a first planar surface, at least one of said isolation trenches receiving a material that is oxidizable in an oxygen containing atmosphere at an elevated temperature, said method comprising a sequence of process steps after forming at least two vertical insulating layers in said at least one of said isolation trenches and a horizontal insulating layer on said first planar surface to provide a second planar surface of an insulating layer above said first planar surface, said sequence comprising:

filling said at least one isolation trench with a fill material until a deepest point of an indentation in a resulting fill material layer formed on said first planar surface has a first level that is above a second level defined by said second planar surface;

performing a first planarization of said resulting fill material layer;

removing a first portion of fill material in said at least one of said isolation trenches by a first over-removal down to a defined depth <u>not deeper than down to half</u> of a trench depth;

removing a portion of at least the vertical insulating layers and over-removing a further portion of the fill material so as to reach a height level substantially equal with said vertical insulating layers within said at least one of said isolation trenches;

depositing at least one cap layer having a thickness extending above said first planar surface and extending downward to said vertical insulating layers and said fill

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material within said at least one of said isolation trenches; and

performing a further planarization of said cap layer by one of a chemical mechanical polishing process and a resist planarization process to form a cover.

Replace claim 26, with the following:

26. (Currently Amended) A wafer for integrated circuits comprising low voltage elements and high voltage elements, wherein chip regions of different potentials are separated by dielectrically insulating regions formed as isolation trenches extending downward from a first planar surface, at least one of said isolation trenches receiving a material that is oxidizable in an oxygen containing atmosphere at an elevated temperature and two vertical insulating layers formed in said at least one of said isolation trenches and a horizontal insulating layer on said first planar surface to provide a second planar surface of an insulating layer above said first planar surface prepared by a process comprising the steps of:

filling said at least one isolation trench with a fill material until a deepest point of an indentation in a resulting fill material layer formed on said first planar surface has a first level that is above a second level defined by said second planar surface;

performing a first planarization of said resulting fill material layer;

removing a first portion of fill material in said at least one of said isolation trenches by a first over-removal down to a defined depth <u>not deeper than down to half of a trench</u> depth;

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removing a portion of at least the vertical insulating layers and over-removing a further portion of the fill material so as to reach a height level substantially equal with said vertical insulating layers within said at least one of said isolation trenches;

depositing at least one cap layer having a thickness extending above said first planar surface and extending downward to said vertical insulating layers and said fill material within said at least one of said isolation trenches; and

performing a further planarization of said cap layer by one of a chemical mechanical polishing process and a resist planarization process to form a cover.

Replace claim 31, with the following:

31. (Currently Amended) A method of forming electric circuits, said electric circuits having integrated therein low voltage logic elements and high voltage power elements and having chip regions of different potentials being separated from one another by dielectrically insulating isolation trenches extending from a planar surface and including materials capable of oxidizing at elevated temperatures in an oxygen containing atmosphere, said method including forming insulating layers and further comprising:

filling said isolation trenches with fill material until a deepest portion of indentations of formed fill material layers are positioned above a planar surface defined by said insulating layers;

planarizing the fill material;

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removing said fill material in said isolation trenches to a defined depth <u>not deeper</u> than down to half of a trench depth by over-etching;

etching said insulating layers and over-etching said fill material so as to obtain a substantially equal height level of said insulating layers and said fill material within said isolation trenches:

depositing at least one of a cap layer and a layer system with a thickness that extends above the level of said planar surface, said at least one of the cap layer and the layer system is an oxygen impermeable layer comprised of silicon nitride; and

planarizing said at least one of the cap layer and the layer system by at least one of a chemical mechanical polishing and a resist planarization process.

Allowable Subject Matter

Claims 1-20, 22-26, 29, 31-32 and 34-37 are allowed.

The following is an examiner's statement of reasons for allowance: The closest prior art known to the Examiner is listed on the PTO 892 forms of record.

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: McNeil et al. (US Pub # 2004/0248375).

McNeil et al. teach forming at least two vertical insulating layers in at least one of isolation trenches, filling at least one isolation trench with a fill material and performing a planarization of fill material layer, but do not teach removing a first portion of fill material in at least one of isolation trenches by a first over-removal down to a defined depth not deeper than down to half of a trench depth, removing a portion of at least the vertical

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insulating layers and over-removing a further portion of the fill material so as to reach a height level substantially equal with vertical insulating layers within at least one of isolation trenches and at least one of the cap layer and the layer system is an oxygen impermeable layer comprised of silicon nitride and planarizing at least one of the cap layer and the layer system by at least one of a chemical mechanical polishing and a resist planarization process.

With respect to independent claim 1, the cited prior art does not anticipate or make obvious, *inter alia*, removing a first portion of fill material in at least one of isolation trenches by a first over-removal down to a defined depth not deeper than down to half of a trench depth, removing a portion of at least the vertical insulating layers and over-removing a further portion of the fill material so as to reach a height level substantially equal with vertical insulating layers within at least one of isolation trenches, depositing at least one cap layer having a thickness extending above first planar surface and extending downward to vertical insulating layers and fill material within at least one of isolation trenches and performing a further planarization of cap layer by one of a chemical mechanical polishing process and a resist planarization process to form a cover.

With respect to independent claim 26, the cited prior art does not anticipate or make obvious, inter alia, removing a first portion of fill material in at least one of isolation trenches by a first over-removal down to a defined depth not deeper than down to half of a trench depth, removing a portion of at least the vertical insulating layers and

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over-removing a further portion of the fill material so as to reach a height level substantially equal with vertical insulating layers within at least one of isolation trenches, depositing at least one cap layer having a thickness extending above first planar surface and extending downward to vertical insulating layers and fill material within at least one of isolation trenches and performing a further planarization of cap layer by one of a chemical mechanical polishing process and a resist planarization process to form a cover.

With respect to independent claim 31, the cited prior art does not anticipate or make obvious, *inter alia*, removing fill material in isolation trenches to a defined depth not deeper than down to half of a trench depth by over-etching, etching insulating layers and over-etching fill material so as to obtain a substantially equal height level of insulating layers and fill material within isolation trenches, depositing at least one of a cap layer and a layer system with a thickness that extends above the level of planar surface, at least one of the cap layer and the layer system is an oxygen impermeable layer comprised of silicon nitride and planarizing at least one of the cap layer and the layer system by at least one of a chemical mechanical polishing and a resist planarization process.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to MOHSEN AHMADI whose telephone number is (571)272-5062. The examiner can normally be reached on Mon-Fri 8:00am-5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Charles Garber can be reached on 1-571-272-2194. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/M. A./ Examiner, Art Unit 2812

/Charles D. Garber/ Supervisory Patent Examiner, Art Unit 2812